ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
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NTE22
Silicon NPN Transistor
AF PO, General Purpose Amp, Driver

Features:

- High Breakdown Voltage: V_{CEO} = 80V
- Large I_C Capacity: I_C = 1A DC
- Good h_{FE} Linearity
- Low Collector Saturation Voltage

Applications:

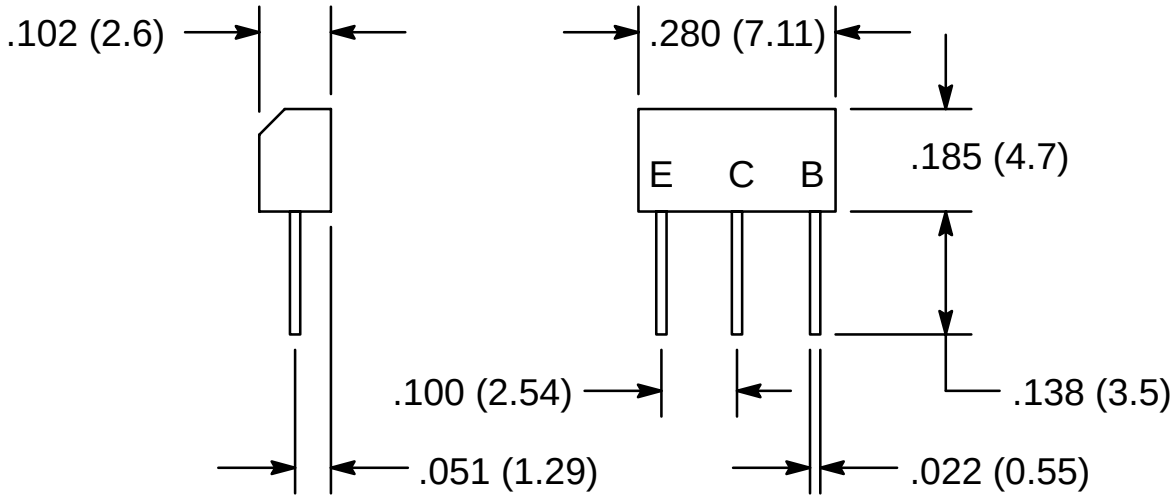
- Medium Power Output Stages
- High–Voltage Drivers

Absolute Maximum Ratings:

Collector–Base Voltage, V_{CBO} 100V
Collector–Emitter Voltage, V_{CEO} 80V
Emitter–Base Voltage, V_{EBO} 5V
Collector Current, I_C
Continuous 1A
Pulse (Note 1) 2A
Collector Dissipation, P_C 900mW
Junction Temperature, T_j . . . . . +135°C
Storage Temperature Range, T_{stg} . . . . . –55° to +125°C
Note 1. P_W = 20ms, Duty Cycle = 1/2

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1mA	80	–	–	V
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 50μA	100	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 50μA	5	–	–	V
Collector Cutoff Current	I_{CBO}	V_{CB} = 80V	–	–	1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V	–	–	1	μA
DC Current Gain	h_{FE}	V_{CE} = 3V, I_C = 50mA	120	–	270	
Collector Saturation Voltage	$V_{CE(sat)}$	I_C = 500A, I_B = 50mA	–	0.15	0.4	V
Transition Frequency	f_T	V_{CE} = 10V, I_C = 50mA	–	100	–	MHz
Output Capacitance	C_{ob}	V_{CB} = 10V, f = 1MHz	–	20	–	pF


.102 (2.6)
.280 (7.11)
.185 (4.7)
E
C
B
.100 (2.54)
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.022 (0.55)